



INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶ : C11D 7/26, 7/32, 7/60, B08B 3/08	A1	(11) International Publication Number: WO 98/45399 (43) International Publication Date: 15 October 1998 (15.10.98)
(21) International Application Number: PCT/US98/05150 (22) International Filing Date: 17 March 1998 (17.03.98) (30) Priority Data: 08/833,382 4 April 1997 (04.04.97) US (71) Applicant: EKC TECHNOLOGY, INC. [US/US]; 2520 Barrington Court, Hayward, CA 94545 (US). (72) Inventors: LEE, Wai, Mun; 40898 Abuelo Way, Fremont, CA 94539 (US). CHEN, Zhefei, Jessie; 34303 Kenwood Drive, Fremont, CA 94555 (US). (74) Agents: HIGGINS, Willis, E.; Cooley Godward LLP, Five Palo Alto Square, 3000 El Camino Real, Palo Alto, CA 94306-2155 (US) et al.		(81) Designated States: JP, KR, SG, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report.</i> <i>With amended claims and statement.</i>  *162162*  *G00001*
(54) Title: ETHYLENEDIAMINETETRAACETIC ACID OR ITS AMMONIUM SALT SEMICONDUCTOR PROCESS RESIDUE REMOVAL COMPOSITION AND PROCESS (57) Abstract An ethylenediaminetetraacetic acid or a mono- di- tri- or tetraammonium salt 5 thereof residue cleaning composition removes photoresist and other residue from integrated circuit substrates. The balance of the composition is desirably made up of water, preferably high purity deionized water, or another suitable polar solvent. A process for removing photoresist or other residue from a substrate, such as an integrated circuit semiconductor wafer including titanium metallurgy, comprises contacting the substrate with the composition for a time and at a temperature sufficient to remove the photoresist or other residue from the substrate. Use of the ethylenediaminetetraacetic acid or a mono- di- tri- or tetraammonium salt thereof in the composition and process provides superior residue removal without attacking titanium or other metallurgy, oxide or nitride layers on the substrate.		

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